

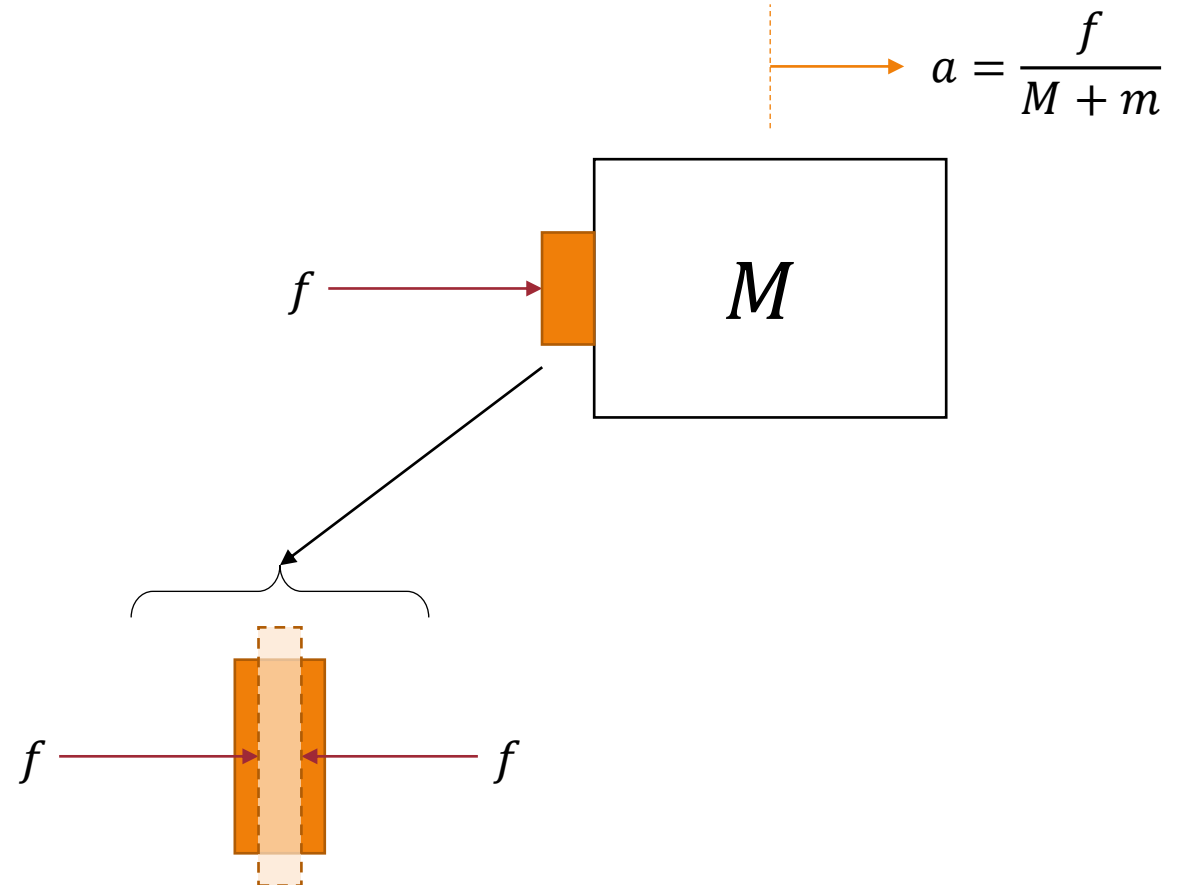
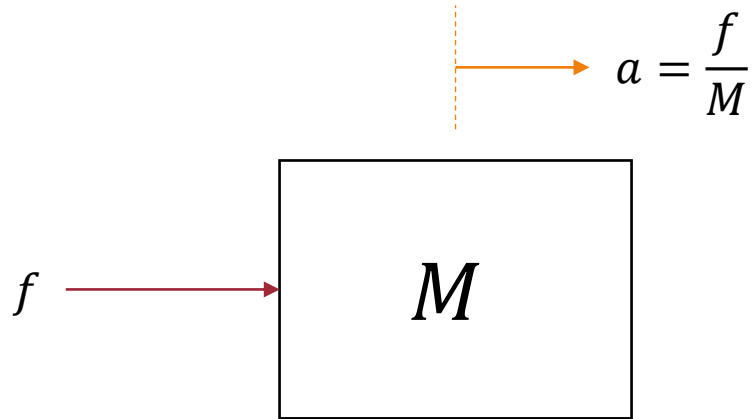
# Transducers & Instrumentation

Module 04

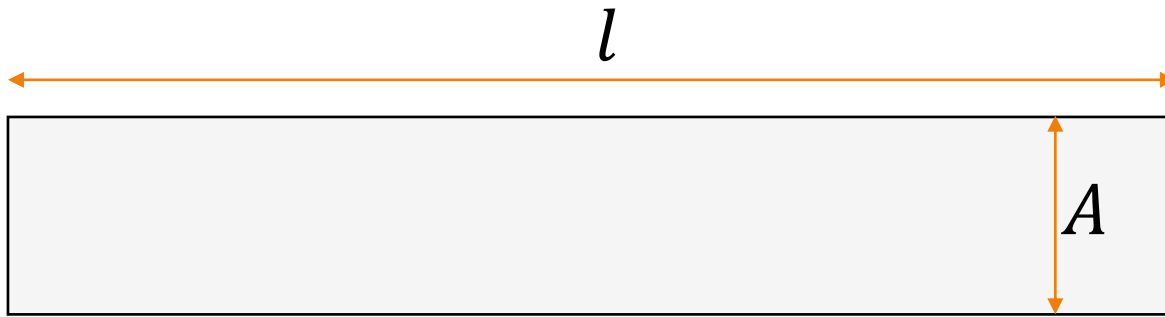
Measuring Forces and Torques

# Forces and Torques

- Forces and torques cause bodies to undergo linear or rotational acceleration.
- Cause deformation.



# Resistance of a material



$$\frac{dR}{R} = S_s \cdot \varepsilon$$

Gauge factor  $\nearrow$   $S_s$   $\nwarrow$  Strain  $\left( \varepsilon = \frac{dl}{l} \right)$

$$R = \rho \frac{l}{A}$$

$$\frac{dR}{R} = \frac{d\rho}{\rho} + \frac{dl}{l} (1 + 2\nu)$$

Piezoresistivity  $\nearrow$   $\frac{d\rho}{\rho}$   $\nwarrow$  Geometric factor  $\nearrow$   $(1 + 2\nu)$

$$S_s = \frac{d\rho/\rho}{\varepsilon} + (1 + 2\nu)$$

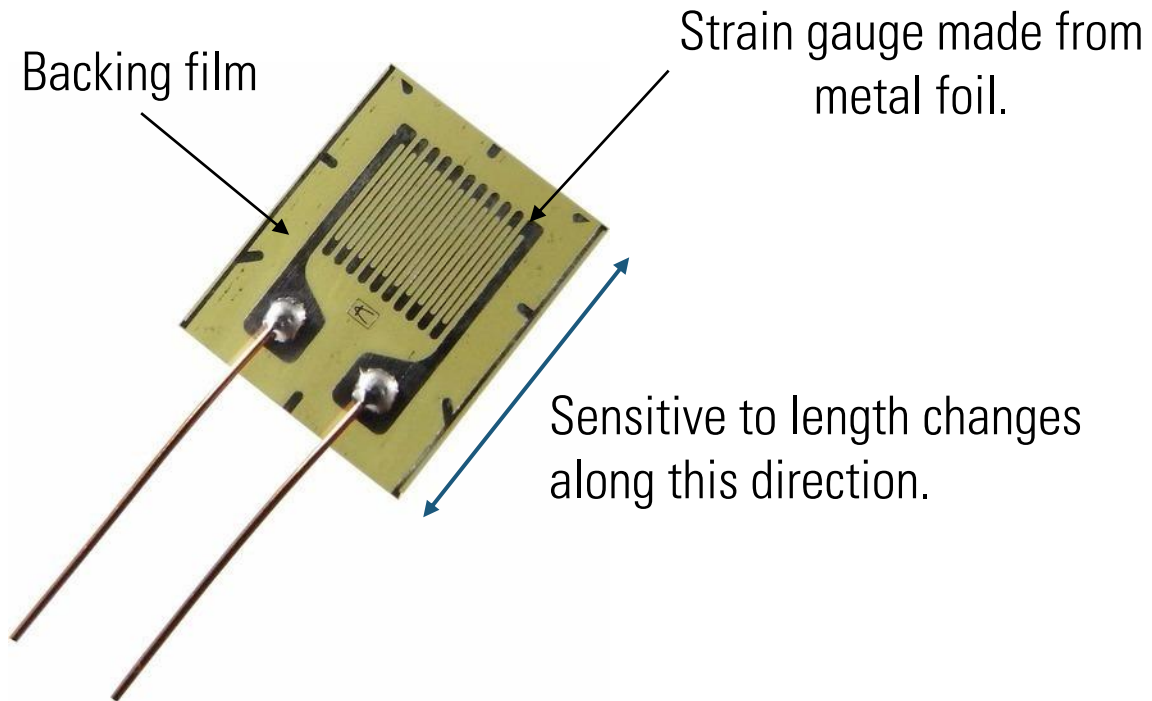
# Gauge factors of common metals

Material	Sensitivity ( $S_s$ )
Platinum (Pt 100%)	6.1
Platinum-Iridium (Pt 95%, Ir 5%)	5.1
Platinum-Tungsten (Pt 92%, W 8%)	4.0
Isoelastic (Fe 55.5%, Ni 36% Cr 8%, Mn 0.5%) *	3.6
Constantan / Advance / Copel (Ni 45%, Cu 55%) *	2.1
Nichrome V (Ni 80%, Cr 20%) *	2.1
Karma (Ni 74%, Cr 20%, Al 3%, Fe 3%) *	2.0
Armour D (Fe 70%, Cr 20%, Al 10%) *	2.0
Monel (Ni 67%, Cu 33%) *	1.9
Manganin (Cu 84%, Mn 12%, Ni 4%) *	0.47
Nickel (Ni 100%)	-12.1

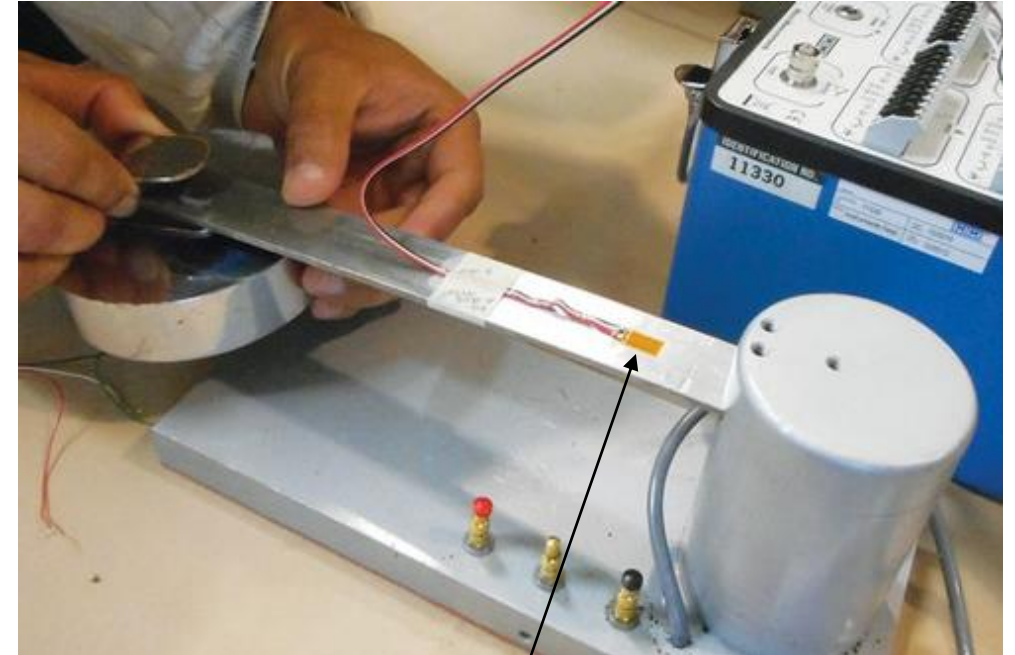
Source: [https://www.efunda.com/designstandards/sensors/strain\\_gages/strain\\_gage\\_sensitivity.cfm](https://www.efunda.com/designstandards/sensors/strain_gages/strain_gage_sensitivity.cfm)

# Strain gauges

Source: <https://5.imimg.com/data5/BG/MR/MY-41643329/strain-gauge-500x500.jpg>



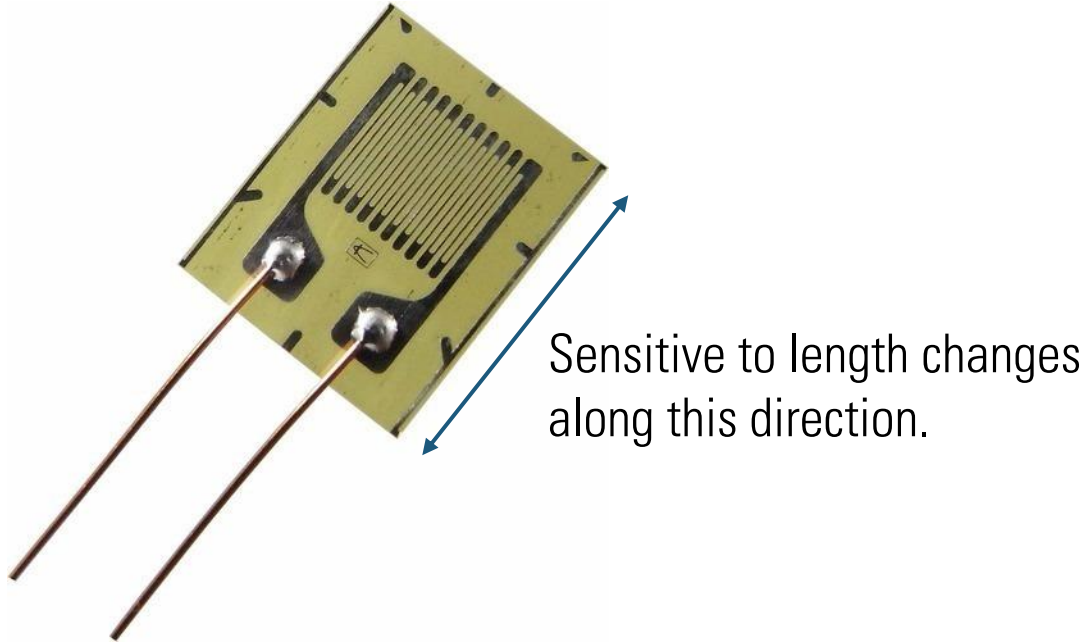
Source: [https://resourcespace-prod.s3.amazonaws.com/rs/filestore/1/1/6/3/9\\_981464e59f794c3/116391ai\\_b5fc4cbf03762f5.jpg](https://resourcespace-prod.s3.amazonaws.com/rs/filestore/1/1/6/3/9_981464e59f794c3/116391ai_b5fc4cbf03762f5.jpg)



Strain gauge bonded to a cantilever.

# Strain gauges

Source: <https://5.imimg.com/data5/BG/MR/MY-41643329/strain-gauge-500x500.jpg>



Problem:

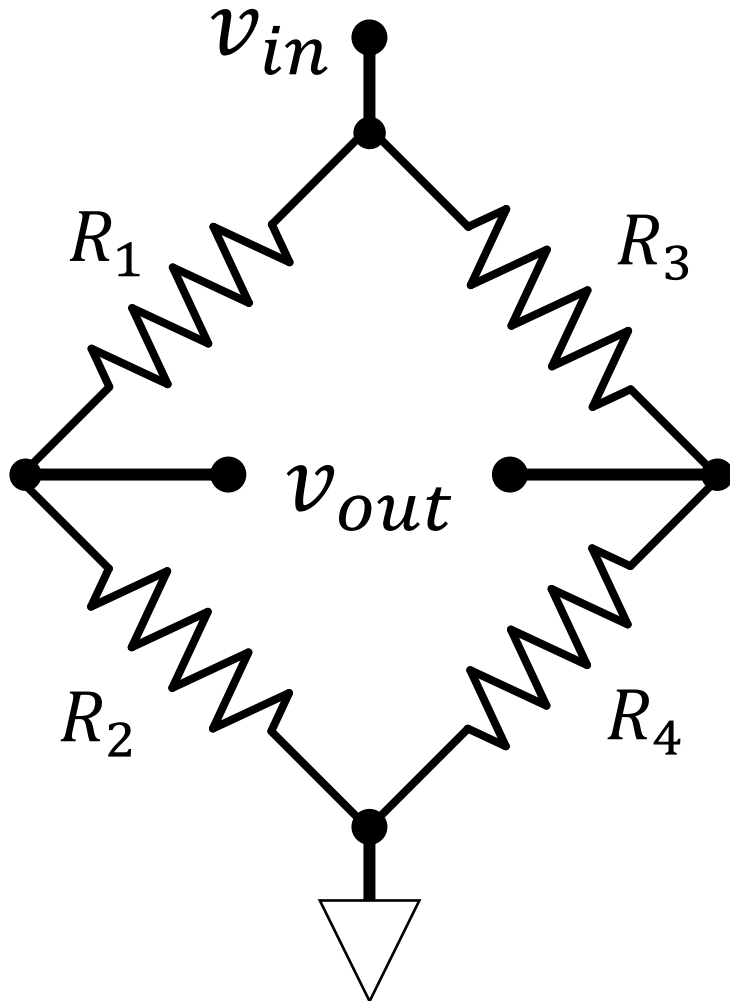
Strain gauge with GF 2.5 and resistance 150 ohms.

Experiences a 400 micro-strain

What is the change in resistance of the strain gauge?

# Measuring resistance change of strain gauges

- Wheatstone Bridge

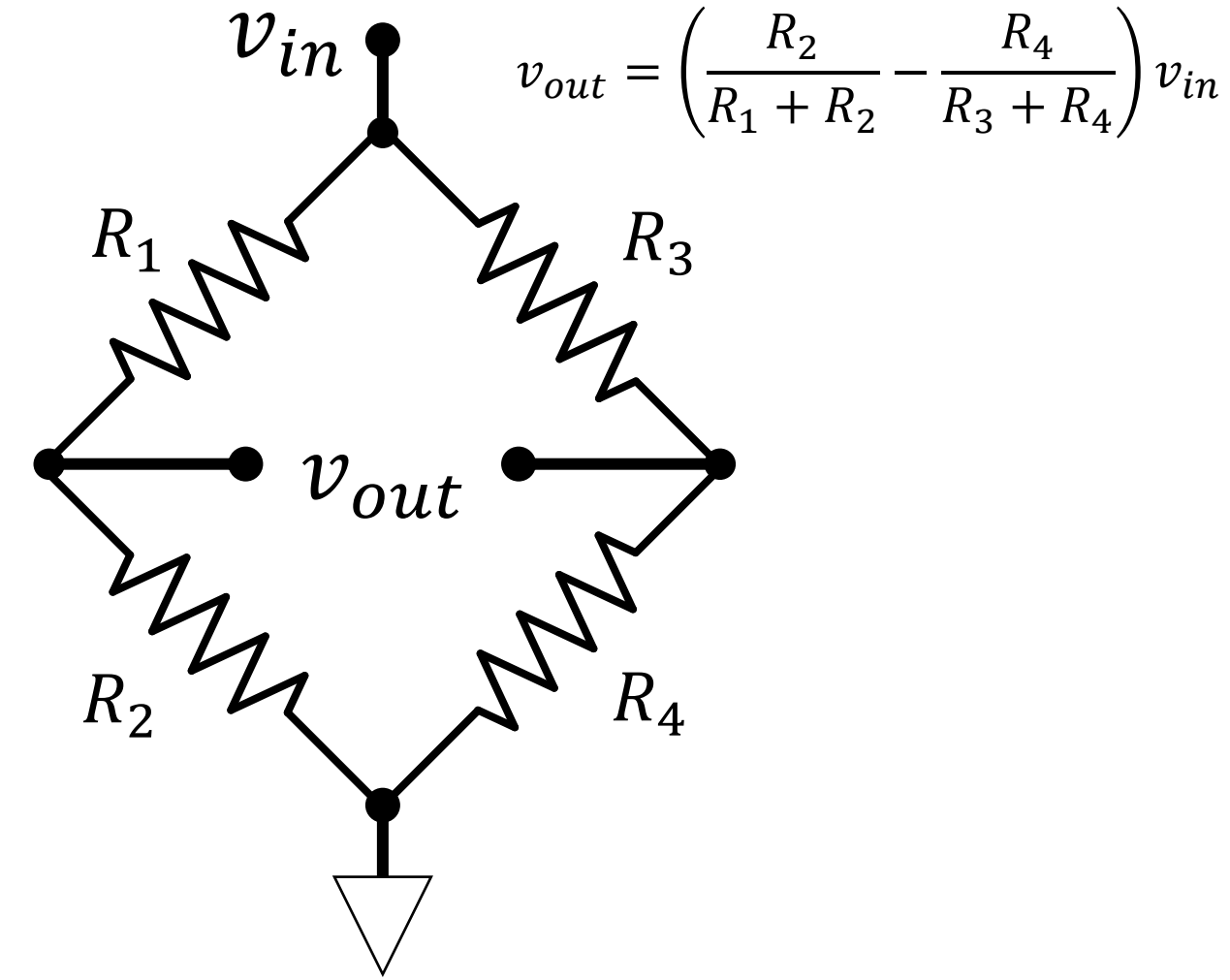


$$v_{out} = \left( \frac{R_2}{R_1 + R_2} - \frac{R_4}{R_3 + R_4} \right) v_{in}$$

$$v_{out} = \frac{R_2 R_3 - R_1 R_4}{(R_1 + R_2)(R_3 + R_4)} v_{in}$$

The bridge is balanced when,  $\frac{R_1}{R_2} = \frac{R_3}{R_4}$ .

# Wheatstone bridge with a single strain gauge



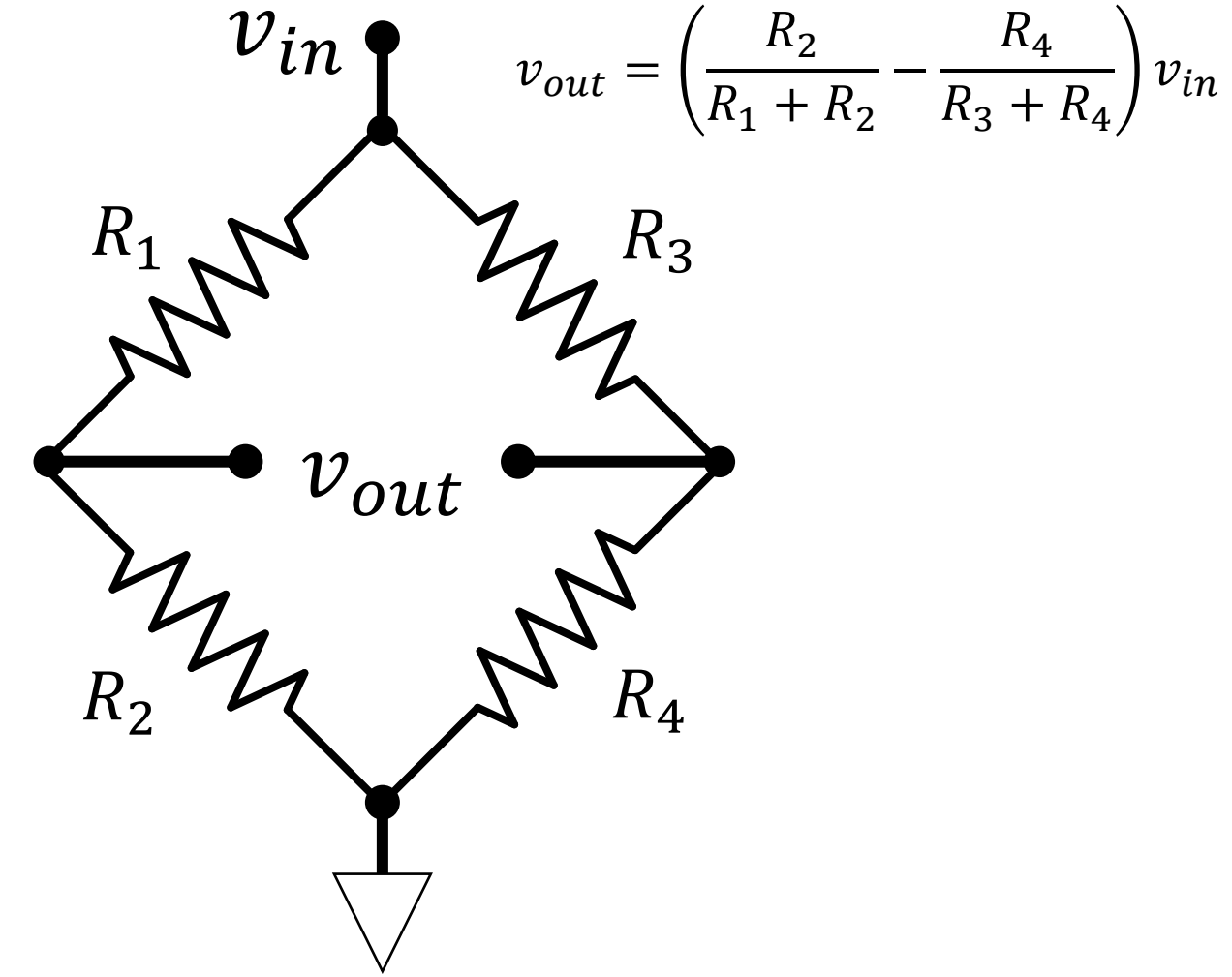
$$R_1 = R_2 = R_3 = R_4 = R$$

Let's assume  $R_2$  changes by  $\Delta R$ .

$$\frac{\Delta v_o}{v_i} = \frac{\Delta R}{4 \left( R + \frac{\Delta R}{2} \right)}$$

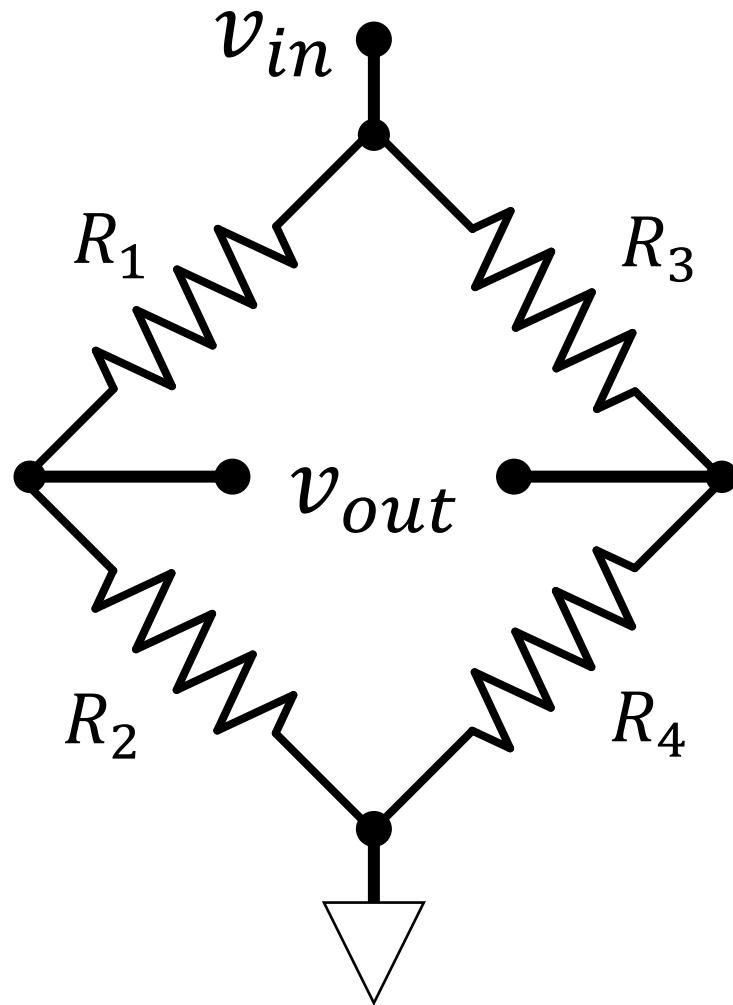


# Wheatstone bridge with a single strain gauge



$$R_1 = R_2 = R_3 = R_4 = R$$

# Bridge Constant ( $k$ ) & Calibration Constant ( $C$ )

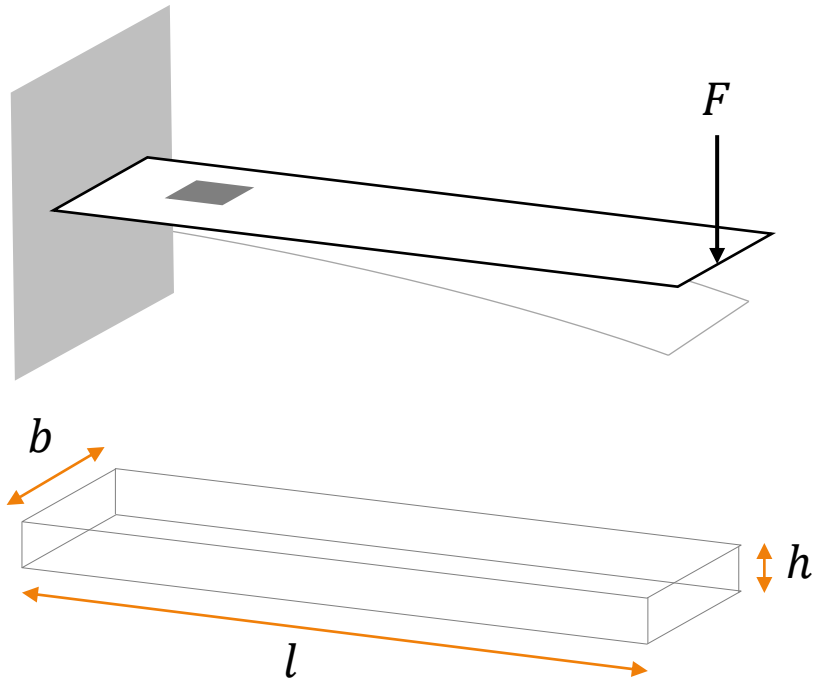


$$\frac{\Delta v_o}{v_i} = k \frac{\Delta R}{4R'}$$

$$\frac{\Delta v_o}{v_i} = C \cdot \varepsilon = \frac{k}{4} S_s$$

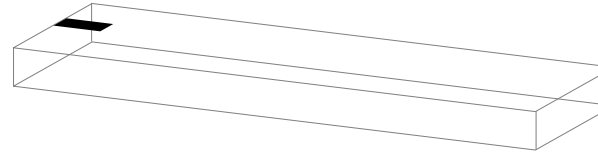
# Some load-cell configurations

## Cantilever based load-cell

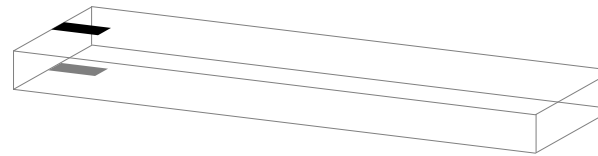


$$\sigma = \frac{6Fl}{bh^2} \quad \varepsilon = E\sigma$$

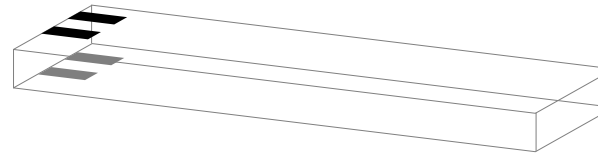
## Single strain gauge



## Double strain gauges

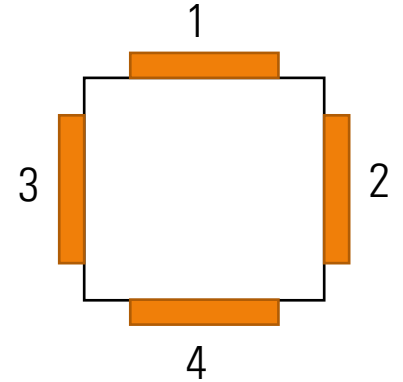
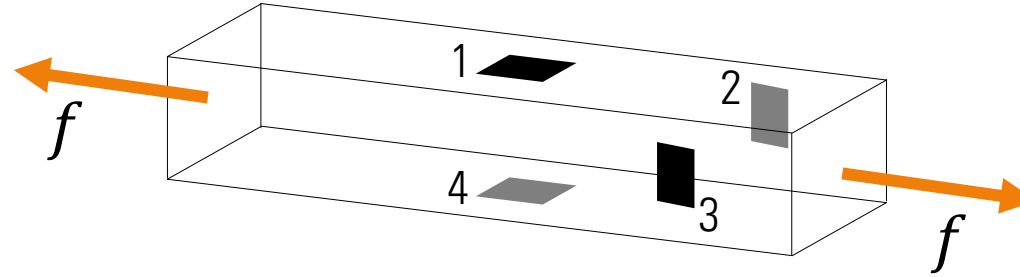
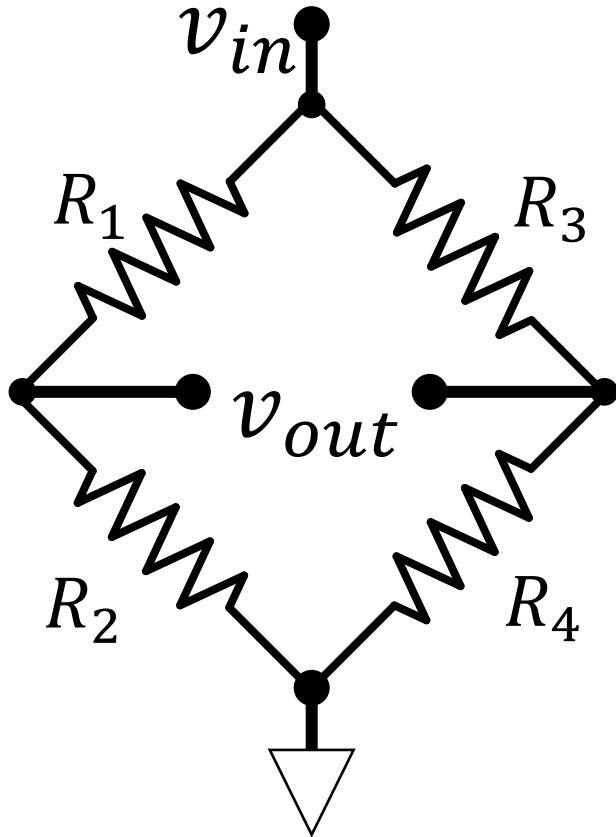


## Four strain gauges



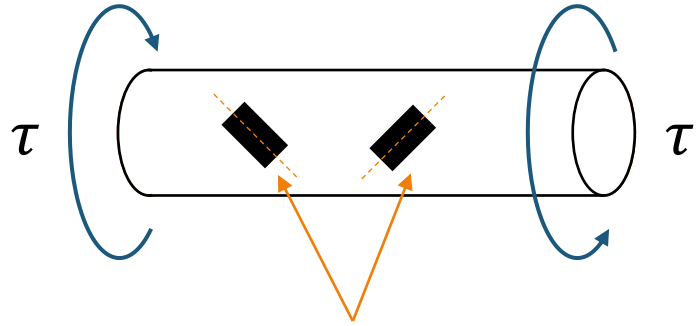
# Some load-cell configurations

Tension/compression  
load-cell



$$\frac{\delta v_{out}}{v_{in}} = 2(1 + \nu) \frac{\delta R}{R'}$$

# Strain gauge torque sensors



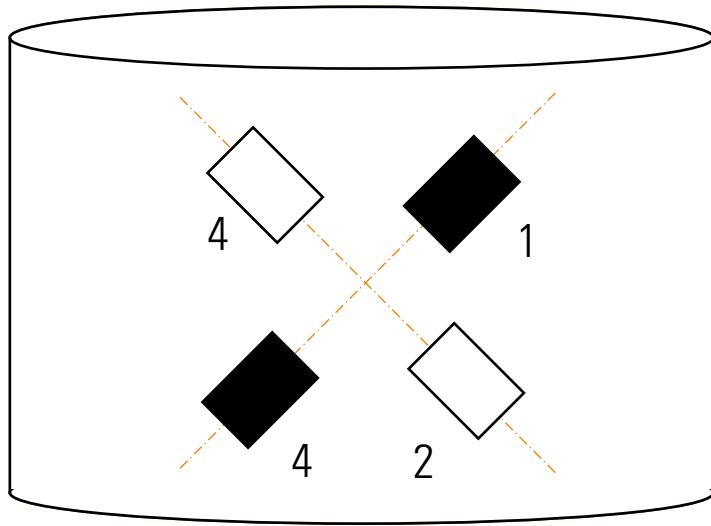
Directions of maximum tensile stresses.

$$T = \frac{\tau r}{J}$$

$$\varepsilon = \frac{r}{2GJ} \tau$$

Torque computed from

$$\tau = \frac{8GJ}{JS_s r} \frac{\delta v_{out}}{v_{in}}$$



# Semiconductor strain gauges

- Highly sensitive to small strains compared to metallic foil strain gauges.

$$\frac{dR}{R} = \frac{d\rho}{\rho} + \frac{dl}{l} (1 + 2\nu)$$

- Change of resistivity due to a mechanical strain: **Piezo-resistivity**.

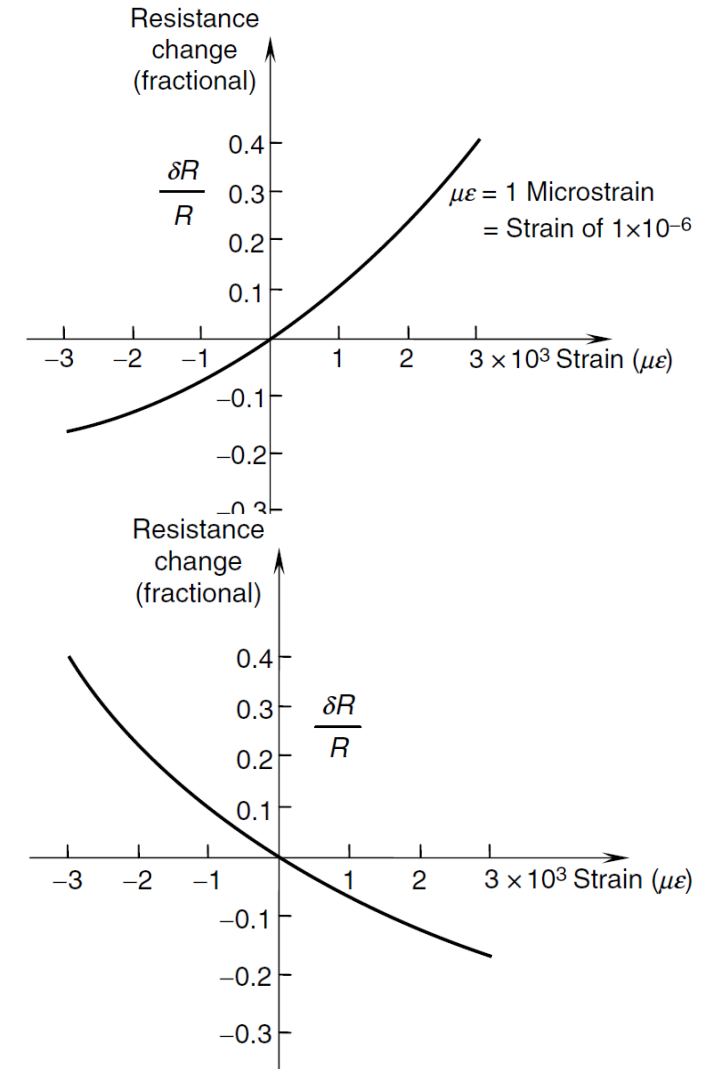
$$\rho_{\varepsilon} = \frac{d\rho/\rho}{\varepsilon}$$

- Gauge factor: 100 to 170 for p-type Silicon, -140 to -100 for n-type Silicon.
- Higher resistivity, lower power consumption, lower heat dissipation.
- Metal foil strain gauge: 150-350 ohms, SC strain gauge: 5000 ohms

# Semiconductor strain gauges

- Some disadvantages:
  - Non-linear strain-resistance relationship.
  - Brittle and difficult to mount on curved surfaces.
  - Max. measurable strain is an order of magnitude lower.
  - Costly
  - More sensitive to temperature.
- Normalized resistance change of SC strain gauges:

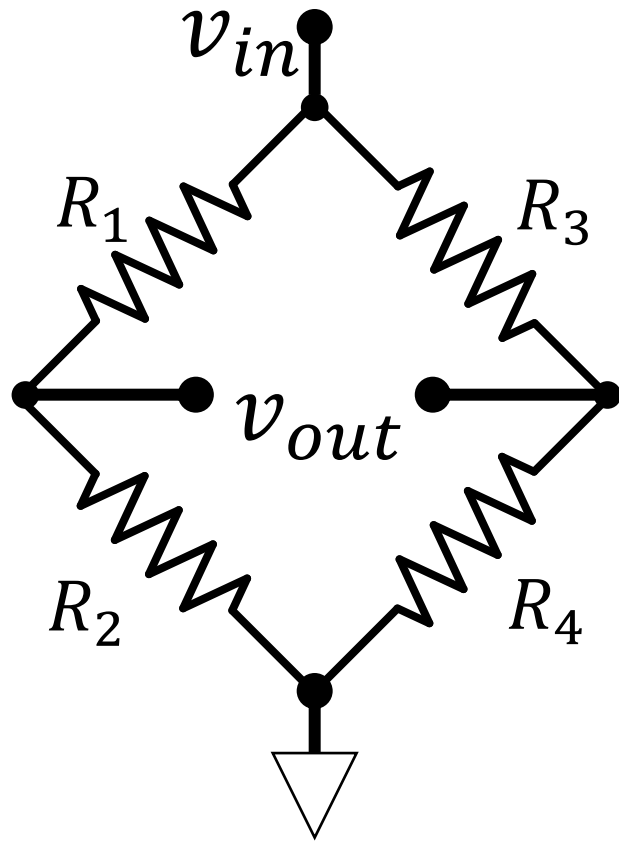
$$\frac{dR}{R} = S_1 \varepsilon + S_2 \varepsilon^2$$



Source: De Silva, C W, Sensors and Actuators, CRC Press (2007)

# Temperature compensation

$$\Delta R = \Delta R_s + \Delta R_T$$





# Temperature compensation

- Resistance of materials are sensitive to temperature.
- Resistivity changes with temperature.

$$\rho_T = \rho_0 \cdot (1 + \alpha \cdot \Delta T)$$

This linear approximation works when  $\alpha \cdot \Delta T \ll 1$ .

- Semiconductor strain gauges are more sensitive than metal foil strain gauges.
- For semiconductor strain gauges the resistance change is larger, and the gauge factor is also temperature dependent.

$$S_{s_T} = S_{s_0} \cdot (1 + \beta \cdot \Delta T)$$